

FMP07N50E

FUJI POWER MOSFET

Super FAP-E³ series

N-CHANNEL SILICON POWER MOSFET

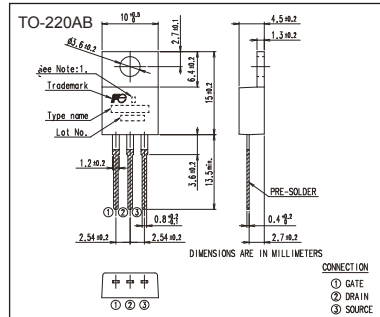
Features

- Maintains both low power loss and low noise
- Lower R_{DS(on)} characteristic
- More controllable switching dv/dt by gate resistance
- Smaller V_{GS} ringing waveform during switching
- Narrow band of the gate threshold voltage (3.0±0.5V)
- High avalanche durability

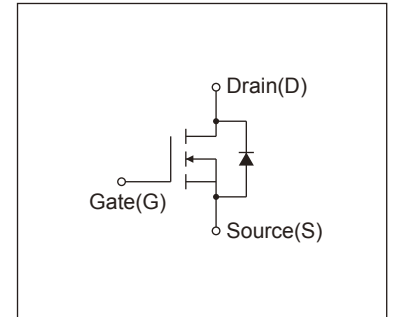
Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

Outline Drawings [mm]



Equivalent circuit schematic



Maximum Ratings and Characteristics

Absolute Maximum Ratings at T_c=25°C (unless otherwise specified)

Description	Symbol	Characteristics	Unit	Remarks
Drain-Source Voltage	V _{DS}	500	V	
	V _{DSDX}	500	V	V _{GS} = -30V
Continuous Drain Current	I _D	±6.5	A	
Pulsed Drain Current	I _{DP}	±26	A	
Gate-Source Voltage	V _{GS}	±30	V	
Repetitive and Non-Repetitive Maximum Avalanche Current	I _{AR}	6.5	A	Note*1
Non-Repetitive Maximum Avalanche Energy	E _{AS}	266	mJ	Note*2
Repetitive Maximum Avalanche Energy	E _{AR}	9.0	mJ	Note*3
Peak Diode Recovery dv/dt	dV/dt	5.4	kV/μs	Note*4
Peak Diode Recovery -di/dt	-di/dt	100	A/μs	Note*5
Maximum Power Dissipation	P _D	2.02	W	T _a =25°C
		90		T _c =25°C
Operating and Storage Temperature range	T _{ch}	150	°C	
	T _{stg}	-55 to +150	°C	

Electrical Characteristics at T_c=25°C (unless otherwise specified)

Description	Symbol	Conditions	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	500	-	-	V
Gate Threshold Voltage	V _{GS(th)}	I _D =250μA, V _{DS} =V _{GS}	2.5	3.0	3.5	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =500V, V _{GS} =0V	-	-	25	μA
		V _{DS} =400V, V _{GS} =0V	-	-	250	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	-	10	100	nA
Drain-Source On-State Resistance	R _{DS(on)}	I _D =3.3A, V _{GS} =10V	-	0.73	0.85	Ω
Forward Transconductance	g _{fs}	I _D =3.3A, V _{DS} =25V	3.5	7	-	S
Input Capacitance	C _{iss}	V _{DS} =25V	-	1050	1575	pF
Output Capacitance	C _{oss}	V _{GS} =0V	-	95	142.5	
Reverse Transfer Capacitance	C _{rss}	f=1MHz	-	7	10.5	
Turn-On Time	td(on)	V _{cc} =300V	-	11	16.5	ns
	tr	V _{GS} =10V	-	7	10.5	
Turn-Off Time	td(off)	I _D =3.3A	-	75	113	
	tf	R _G =10Ω	-	14	21	
Total Gate Charge	Q _G	V _{cc} =250V	-	32	48	nC
Gate-Source Charge	Q _{GS}	I _D =6.5A	-	8	12	
Gate-Drain Charge	Q _{GD}	V _{GS} =10V	-	9	13.5	
Avalanche Capability	I _{AV}	L=4.61mH, T _{ch} =25°C	6.5	-	-	A
Diode Forward On-Voltage	V _{SD}	I _F =6.5A, V _{GS} =0V, T _{ch} =25°C	-	0.86	1.30	V
Reverse Recovery Time	t _{rr}	I _F =6.5A, V _{GS} =0V	-	0.34	-	μs
Reverse Recovery Charge	Q _{rr}	-di/dt=100A/μs, T _{ch} =25°C	-	3.0	-	μC

Thermal Characteristics

Description	Symbol	Test Conditions	min.	typ.	max.	Unit
Thermal resistance	R _{th(ch-c)}	Channel to Case			1.390	°C/W
	R _{th(ch-a)}	Channel to Ambient			62.0	°C/W

Note *1 : T_{ch}≤150°C

Note *2 : Stating T_{ch}=25°C, I_{AS}=2.6A, L=72.1mH, V_{cc}=50V, R_G=50Ω

E_{AS} limited by maximum channel temperature and avalanche current.
See to 'Avalanche Energy' graph.

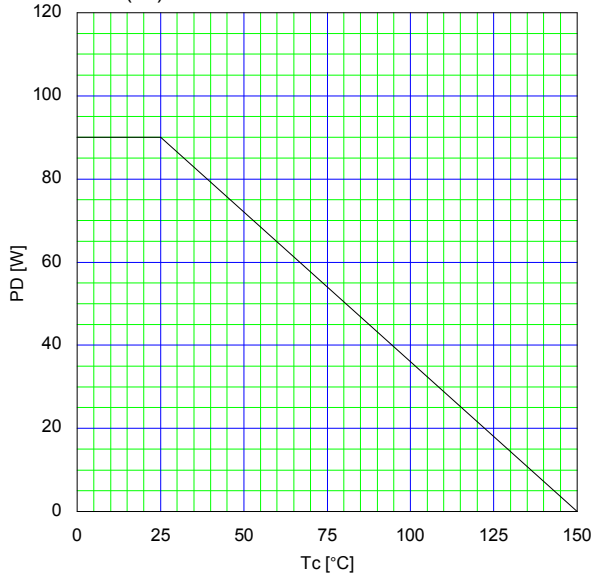
Note *3 : Repetitive rating : Pulse width limited by maximum channel temperature.

See to the 'Transient Thermal Impedance' graph.

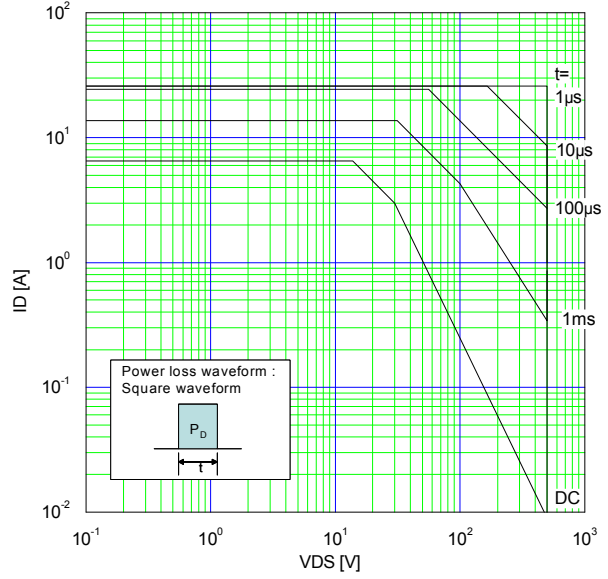
Note *4 : I_F=I_D, -di/dt=100A/μs, V_{cc}≤BV_{DSS}, T_{ch}≤150°C.

Note *5 : I_F=I_D, dv/dt=5.4kV/μs, V_{cc}≤BV_{DSS}, T_{ch}≤150°C.

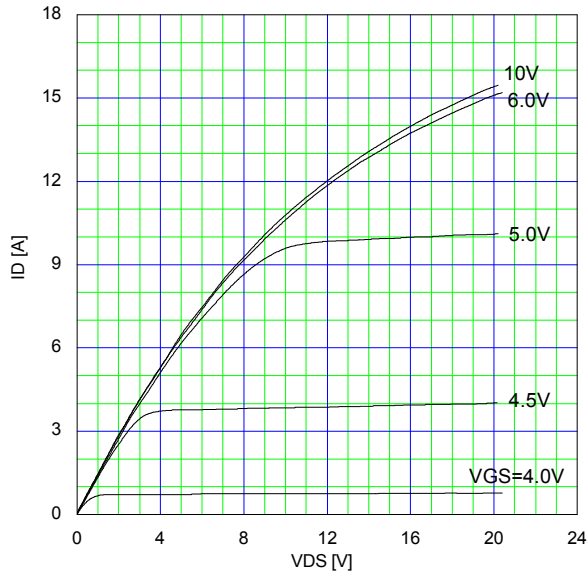
Allowable Power Dissipation
 $P_D = f(T_c)$



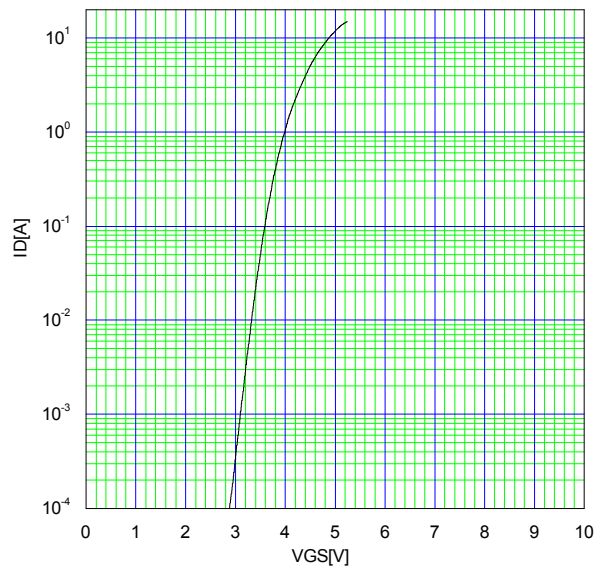
Safe Operating Area
 $I_D = f(V_{DS})$: Duty=0 (Single pulse), $T_c = 25\text{ }^\circ\text{C}$



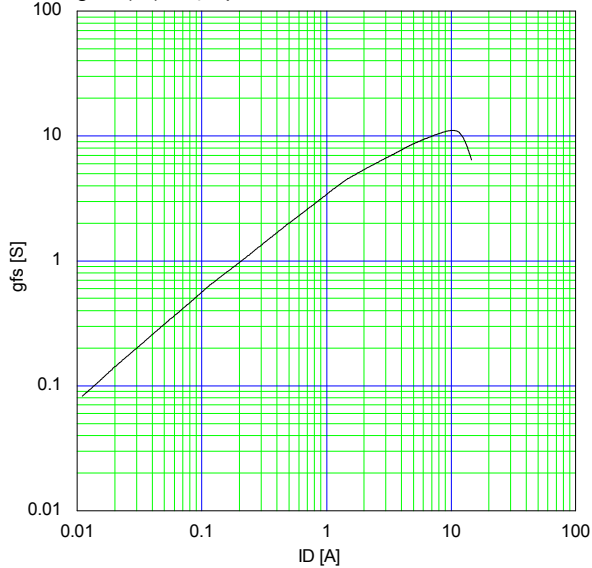
Typical Output Characteristics
 $I_D = f(V_{DS})$: 80 μs pulse test, $T_{ch} = 25\text{ }^\circ\text{C}$



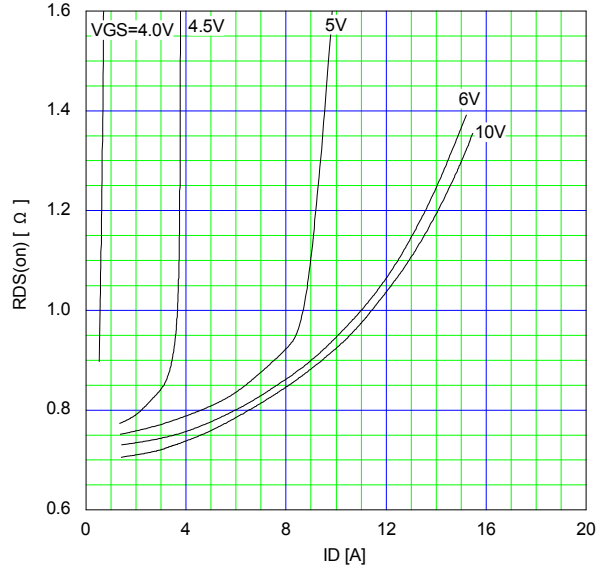
Typical Transfer Characteristic
 $I_D = f(V_{GS})$: 80 μs pulse test, $V_{DS} = 25\text{V}$, $T_{ch} = 25\text{ }^\circ\text{C}$

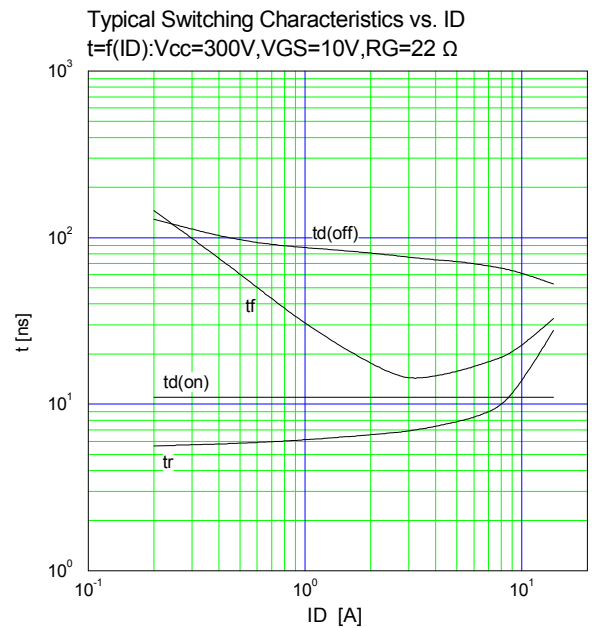
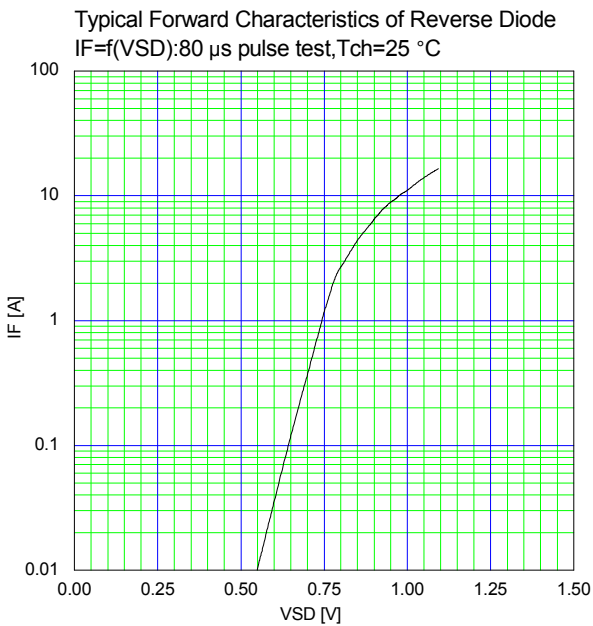
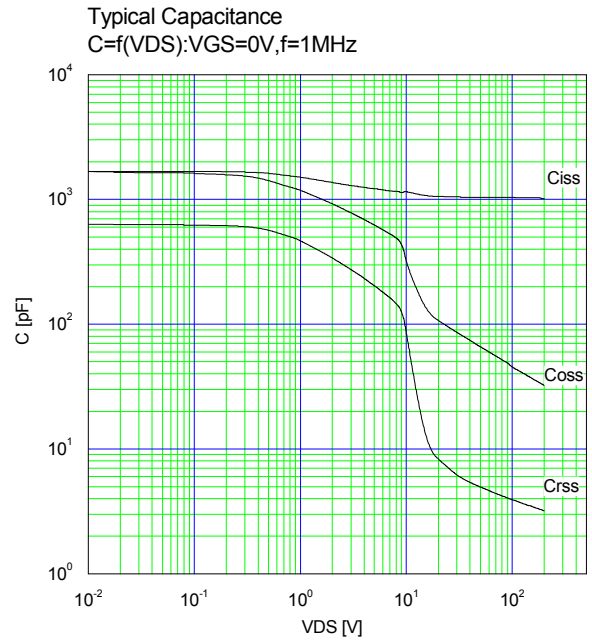
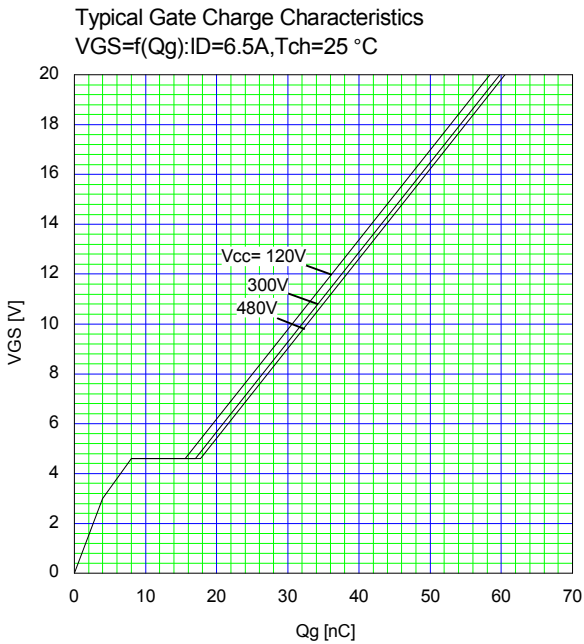
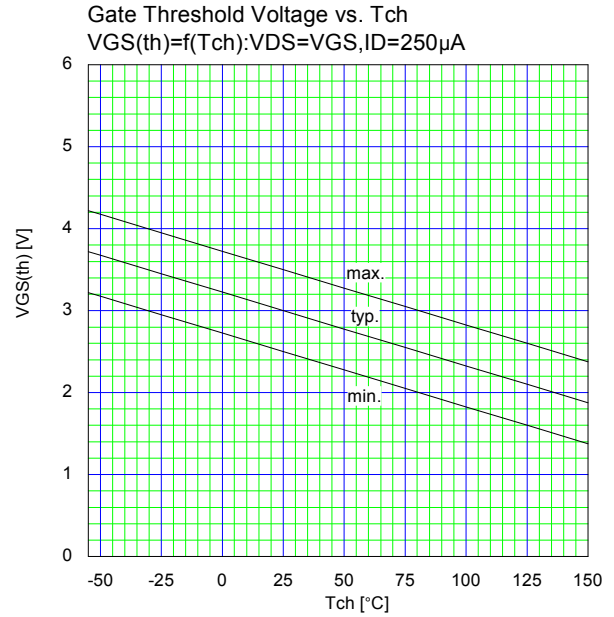
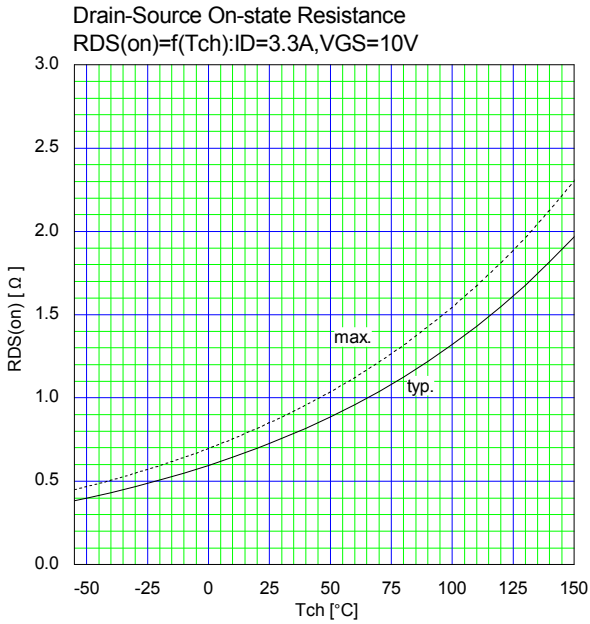


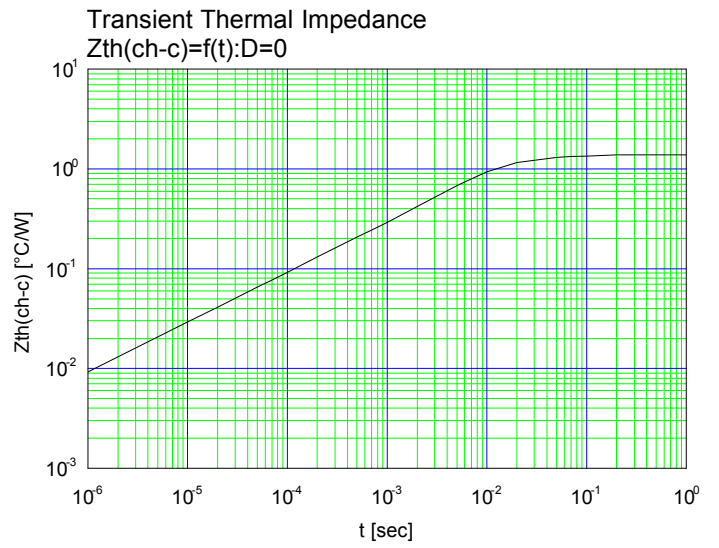
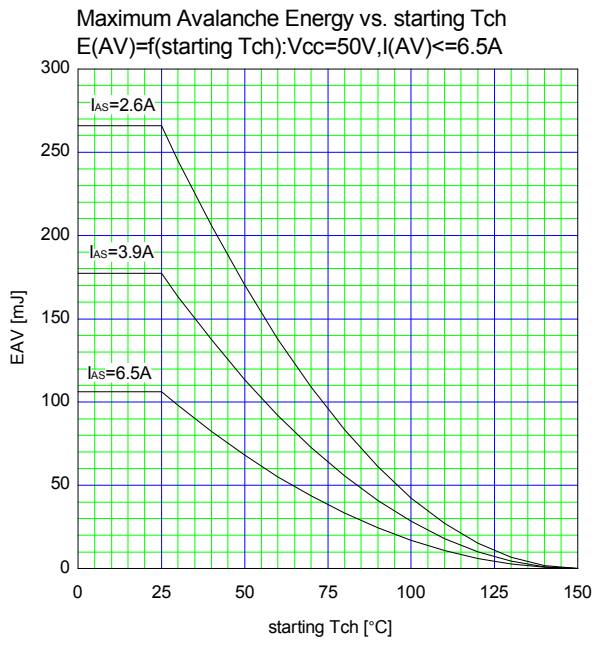
Typical Transconductance
 $g_{fs} = f(I_D)$: 80 μs pulse test, $V_{DS} = 25\text{V}$, $T_{ch} = 25\text{ }^\circ\text{C}$



Typical Drain-Source on-state Resistance
 $R_{DS(on)} = f(I_D)$: 80 μs pulse test, $T_{ch} = 25\text{ }^\circ\text{C}$







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